

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

VEC2415 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · Composite type facilitating high-density mounting
- · 4V drive
- Mounting high 0.75mm
- · Protection diode in

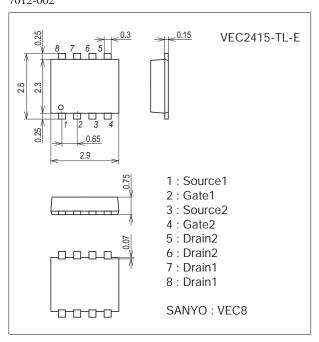
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		60	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	ID		3	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	12	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm) 1unit	0.9	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7012-002



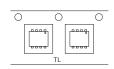
Product & Package Information

• Package : VEC8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

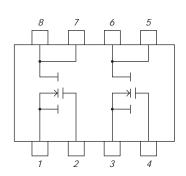
Packing Type: TL





Marking

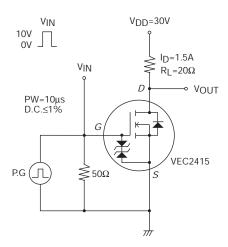
Electrical Connection



Electrical Characteristics at Ta=25°C

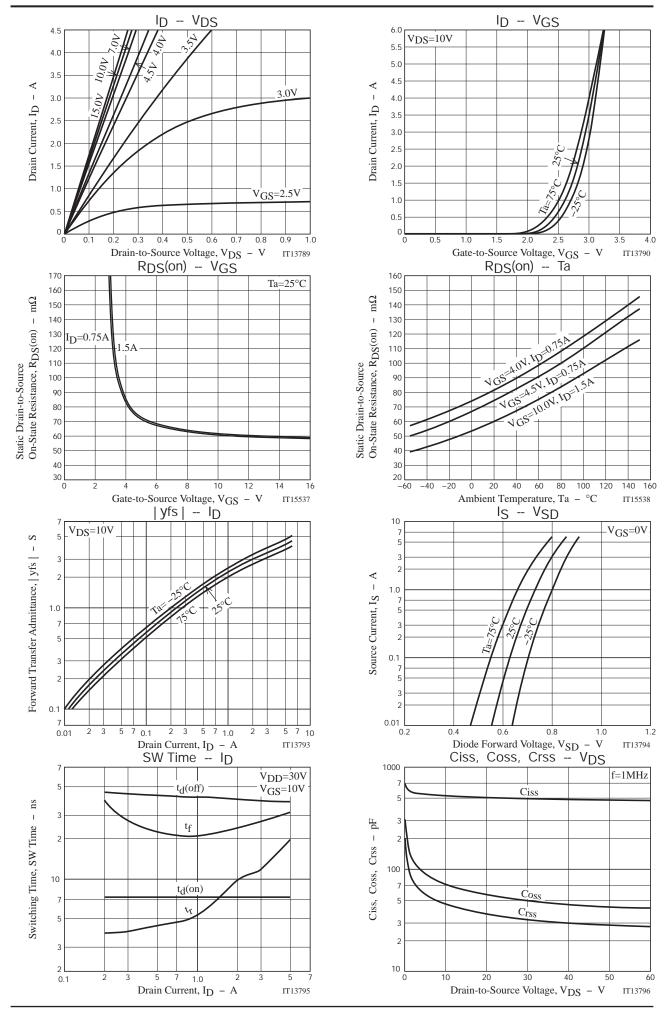
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =60V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	VDS=10V, ID=1.5A		2.6		S	
	R _{DS} (on)1	I _D =1.5A, V _G S=10V		62	80	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =0.75A, V _G S=4.5V		76	106	mΩ	
	R _{DS} (on)3	I _D =0.75A, V _G S=4V		83	116	mΩ	
Input Capacitance	Ciss			505		pF	
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		57		pF	
Reverse Transfer Capacitance	Crss			37		pF	
Turn-ON Delay Time	t _d (on)			7.3		ns	
Rise Time	tr	Considered Took Classick		7.5		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		41		ns	
Fall Time	tf			22		ns	
Total Gate Charge	Qg			10		nC	
Gate-to-Source Charge	Qgs	V _{DS} =30V, V _{GS} =10V, I _D =3A		1.6		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		2.1		nC	
Diode Forward Voltage	V _{SD}	IS=3A, VGS=0V		0.81	1.2	V	

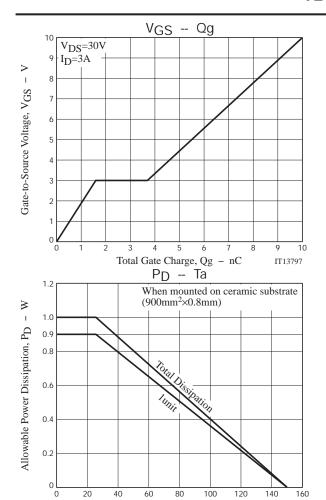
Switching Time Test Circuit



Ordering Information

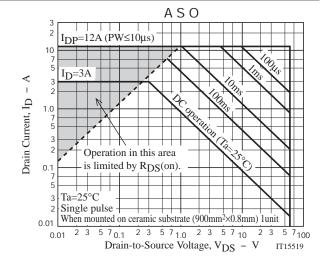
Device	Device Package		memo	
VEC2415-TL-E	VEC8	3,000pcs./reel	Pb Free	





Ambient Temperature, Ta - °C

IT15520

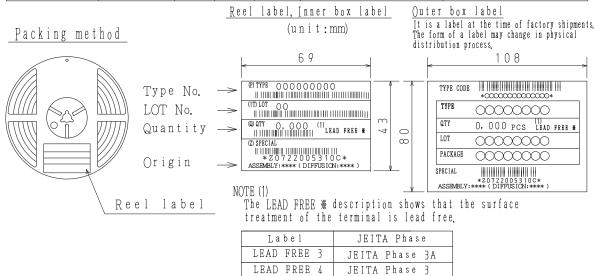


Taping Specification

VEC2415-TL-E

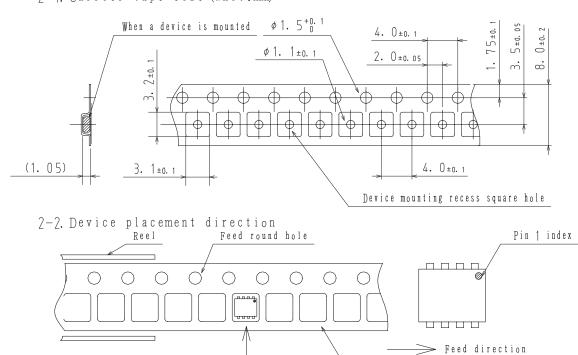
1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
VEC8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



2. Taping configuration

2-1. Carrier tape size (unit:mm)



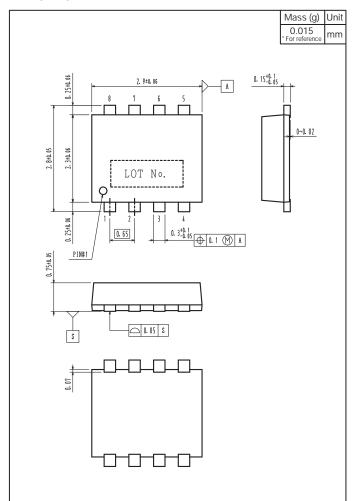
Carrier tape

Those with oen electrode terminal on the feed hole side·····TL

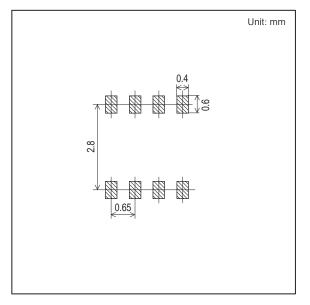
TL

Outline Drawing

VEC2415-TL-E



Land Pattern Example



Note on usage: Since the VEC2415 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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